Andrew J Steckl

List of Publications by Year in Descending Order

331 papers	9,694 citations	53 h-index	84 g-index
360 ext. papers	10,587 ext. citations	4.1 avg, IF	6.61 L-index

#	Paper	IF	Citations
331	Comparative analysis of genome code complexity and manufacturability with engineering benchmarks.. *Scientific Reports*, **2022**, 12, 2808	4.9	
330	Electrospinning of cyanoacrylate tissue adhesives for human dural repair in endonasal surgery. *Journal of Biomedical Materials Research - Part B Applied Biomaterials*, **2021**, 110, 660	3.5	1
329	Controlled drug release of parylene-coated pramipexole nanofibers for transdermal applications. *Surface and Coatings Technology*, **2021**, 409, 126831	4.4	0
328	Quantitative hematocrit measurement of whole blood in a point-of-care lateral flow device using a smartphone flow tracking app. *Biosensors and Bioelectronics*, **2020**, 163, 112300	11.8	9
327	Self-inflating floating nanofiber membranes for controlled drug delivery. *International Journal of Pharmaceutics*, **2020**, 579, 119164	6.5	14
326	Lateral flow assay using aptamer-based sensing for on-site detection of dopamine in urine. *Analytical Biochemistry*, **2020**, 596, 113637	3.1	28
325	and evaluation of microneedles coated with electrosprayed micro/nanoparticles for medical skin treatments. *Journal of Microencapsulation*, **2020**, 37, 517-527	3.4	4
324	Aptamer-Based Lateral Flow Biosensor for Rapid Detection of Salivary Cortisol. *ACS Omega*, **2020**, 5, 32890-32898	3.9	25
323	Label-Free Optical Detection of Multiple Biomarkers in Sweat, Plasma, Urine, and Saliva. *ACS Sensors*, **2019**, 4, 1346-1357	9.2	28
322	Coaxial Electrospinning Formation of Complex Polymer Fibers and their Applications. *ChemPlusChem*, **2019**, 84, 1453-1497	2.8	91
321	Multi-layered core-sheath fiber membranes for controlled drug release in the local treatment of brain tumor. *Scientific Reports*, **2019**, 9, 17936	4.9	25
320	Aptamer-based lateral flow assay for point of care cortisol detection in sweat. *Sensors and Actuators B: Chemical*, **2019**, 283, 79-86	8.5	103
319	Paper Microfluidics for Point-of-Care Blood-Based Analysis and Diagnostics. *Analytical Chemistry*, **2019**, 91, 352-371	7.8	72
318	Engineering a simple lateral flow device for animal blood coagulation monitoring. *Biomicrofluidics*, **2018**, 12, 014110	3.2	6
317	Absorption of Ethylene on Membranes Containing Potassium Permanganate Loaded into Alumina-Nanoparticle-Incorporated Alumina/Carbon Nanofibers. *Journal of Agricultural and Food Chemistry*, **2018**, 66, 5635-5643	5.7	17
316	Stress Biomarkers in Biological Fluids and Their Point-of-Use Detection. *ACS Sensors*, **2018**, 3, 2025-2044	9.2	89
315	Correcting the effect of hematocrit in whole blood coagulation analysis on paper-based lateral flow device. *Analytical Methods*, **2018**, 10, 2869-2874	3.2	8

314	Long-term antimicrobial effect of nisin released from electrospun triaxial fiber membranes. *Acta Biomaterialia*, **2017**, 53, 242-249	10.8	89
313	Stimuli-Responsive Self-Immolative Polymer Nanofiber Membranes Formed by Coaxial Electrospinning. *ACS Applied Materials & Interfaces*, **2017**, 9, 11858-11865	9.5	42
312	Flow reproducibility of whole blood and other bodily fluids in simplified no reaction lateral flow assay devices. *Biomicrofluidics*, **2017**, 11, 024116	3.2	20
311	Engineering DNA and Nucleobases for Present and Future Device Applications **2017**, 191-233		4
310	Point-of-care coagulation monitoring: first clinical experience using a paper-based lateral flow diagnostic device. *Biomedical Microdevices*, **2017**, 19, 64	3.7	26
309	Selective pH-Responsive Core-Sheath Nanofiber Membranes for Chem/Bio/Med Applications: Targeted Delivery of Functional Molecules. *ACS Applied Materials & Interfaces*, **2017**, 9, 42653-42660	9.5	35
308	In-vitro evaluation of MPA-loaded electrospun coaxial fiber membranes for local treatment of glioblastoma tumor cells. *Journal of Drug Delivery Science and Technology*, **2017**, 40, 45-50	4.5	19
307	Quantitative Detection in Lateral Flow Immunoassay Using Integrated Organic Optoelectronics. *IEEE Sensors Journal*, **2017**, 17, 8343-8349	4	5
306	Urine-powered (galvanic) electric cell and sensor on paper substrate. *Flexible and Printed Electronics* , **2016**, 1, 044002	3.1	2
305	Integrated NFC power source for zero on-board power in fluorescent paper-based lateral flow immunoassays. *Flexible and Printed Electronics*, **2016**, 1, 044001	3.1	4
304	Improved Performance of OLEDs on Cellulose/Epoxy Substrate Using Adenine as a Hole Injection Layer. *ACS Photonics*, **2015**, 2, 439-445	6.3	55
303	Electrospun carbon nanofiber modified electrodes for stripping voltammetry. *Analytical Chemistry*, **2015**, 87, 9315-21	7.8	60
302	Integrated OLED as excitation light source in fluorescent lateral flow immunoassays. *Biosensors and Bioelectronics*, **2015**, 74, 150-5	11.8	27
301	Exploring the Potential of Nucleic Acid Bases in Organic Light Emitting Diodes. *Advanced Materials*, **2015**, 27, 7552-62	24	69
300	Organic Light-Emitting Diodes: Exploring the Potential of Nucleic Acid Bases in Organic Light Emitting Diodes (Adv. Mater. 46/2015). *Advanced Materials*, **2015**, 27, 7680-7680	24	1
299	DNA bases thymine and adenine in bio-organic light emitting diodes. *Scientific Reports*, **2014**, 4, 7105	4.9	30
298	Blood coagulation screening using a paper-based microfluidic lateral flow device. *Lab on A Chip*, **2014**, 14, 4035-41	7.2	88
297	Magnetic particles as liquid carriers in the microfluidic lab-in-tube approach to detect phase change. *ACS Applied Materials & Interfaces*, **2014**, 6, 8066-72	9.5	3

296	Microbial Power-Generating Capabilities on Micro-/Nano-Structured Anodes in Micro-Sized Microbial Fuel Cells. *Fuel Cells*, **2014**, 14, 801-809	2.9	29
295	Pentacene organic thin-film transistors on flexible paper and glass substrates. *Nanotechnology*, **2014**, 25, 094005	3.4	41
294	p-type GaN grown by phase shift epitaxy. *Applied Physics Letters*, **2014**, 104, 012108	3.4	5
293	High brightness phosphorescent organic light emitting diodes on transparent and flexible cellulose films. *Nanotechnology*, **2014**, 25, 094012	3.4	55
292	Latest advances in biomaterials: from deoxyribonucleic acid to nucleobases **2014**,		4
291	Triaxial electrospun nanofiber membranes for controlled dual release of functional molecules. *ACS Applied Materials & Interfaces*, **2013**, 5, 8241-5	9.5	150
290	Versatile electrowetting arrays for smart window applications-from small to large pixels on fixed and flexible substrates. *Solar Energy Materials and Solar Cells*, **2013**, 117, 544-548	6.4	15
289	Lightweight electrowetting display on ultra-thin glass substrate. *Journal of the Society for Information Display*, **2013**, 21, 192-197	2.1	12
288	. *IEEE Spectrum*, **2013**, 50, 48-61	1.7	47
287	Investigation of DNA nucleobases-thin films for potential application in electronics and photonics **2013**,		3
286	Enhanced Performance of Micro-Electro-Mechanical-Systems (MEMS) Microbial Fuel Cells Using Electrospun Microfibrous Anode and Optimizing Operation. *Fuel Cells*, **2013**, 13, 336-341	2.9	29
285	Electrowetting on non-fluorinated hydrophobic surfaces. *Journal of the Society for Information Display*, **2013**, 21, 411-416	2.1	1
284	Electrowetting on Flexible Substrates. *Journal of Adhesion Science and Technology*, **2012**, 26, 1931-1939	2	10
283	Photocatalytic cellulosic electrospun fibers for the degradation of potent cyanobacteria toxin microcystin-LR. *Journal of Materials Chemistry*, **2012**, 22, 12666		18
282	Triggered release of molecules across droplet interface bilayer lipid membranes using photopolymerizable lipids. *Langmuir*, **2012**, 28, 7657-64	4	29
281	Nanofiber-Based Bulk-Heterojunction Organic Solar Cells Using Coaxial Electrospinning. *Advanced Energy Materials*, **2012**, 2, 1136-1144	21.8	60
280	Fabrication of natural DNA-containing organic light emitting diodes **2011**,		5
279	Deactivating chemical agents using enzyme-coated nanofibers formed by electrospinning. *ACS Applied Materials & Interfaces*, **2011**, 3, 4633-9	9.5	37

278	Voltage control of droplet interface bilayer lipid membrane dimensions. *Langmuir*, **2011**, 27, 618-26	4	47
277	Immobilization of stable thylakoid vesicles in conductive nanofibers by electrospinning. *Biomacromolecules*, **2011**, 12, 778-84	6.9	17
276	Unidirectional self-patterning of CaF2 nanorod arrays using capillary pressure. *Journal of Materials Research*, **2011**, 26, 223-229	2.5	1
275	Flexible electrowetting and electrowetting on flexible substrates **2011**,		4
274	Eu-Doped GaN Films Grown by Phase Shift Epitaxy. *Applied Physics Express*, **2010**, 3, 121002	2.4	10
273	Electrical and magnetic properties of GaN codoped with Eu and Si. *Journal of Applied Physics*, **2010**, 107, 013901	2.5	14
272	Dose effects in electron beam irradiation of DNA-complex thin films. *Applied Physics Letters*, **2010**, 97, 063702	3.4	3
271	Photocatalytic Self Cleaning Textile Fibers by Coaxial Electrospinning. *ACS Applied Materials & Interfaces*, **2010**, 2, 2448-2455	9.5	123
270	Immunoassay on free-standing electrospun membranes. *ACS Applied Materials & Interfaces*, **2010**, 2, 252-8	9.5	21
269	Complementary electrowetting devices on plasma-treated fluoropolymer surfaces. *Langmuir*, **2010**, 26, 9474-83	4	15
268	Electrowetting on paper for electronic paper display. *ACS Applied Materials & Interfaces*, **2010**, 2, 3318-23	9.5	114
267	Three-color electrowetting display device for electronic paper. *Applied Physics Letters*, **2010**, 97, 023514	3.4	85
266	Effect of growth conditions on Eu3+ luminescence in GaN. *Journal of Crystal Growth*, **2010**, 312, 680-684	1.6	22
265	Direct and indirect photoluminescence excitation and ultraviolet emission from Tm-doped AlxGa1−xN. *Journal of Applied Physics*, **2009**, 105, 083509	2.5	2
264	Effect of Tm3+-induced defects on the photoexcitation energy relaxation in Tm-doped AlxGa1−xN. *Physical Review B*, **2009**, 79,	3.3	8
263	Effect of Si codoping on Eu3+ luminescence in GaN. *Journal of Applied Physics*, **2009**, 105, 043107	2.5	33
262	Deep ultraviolet photoluminescence of Tm-doped AlGaN alloys. *Applied Physics Letters*, **2009**, 94, 111103	3.4	6
261	Optically active centers in Eu implanted, Eu in situ doped GaN, and Eu doped GaN quantum dots. *Journal of Applied Physics*, **2009**, 105, 043104	2.5	37

260	Excitation pathways and efficiency of Eu ions in GaN by site-selective spectroscopy. *Applied Physics B: Lasers and Optics*, **2009**, 97, 607-618	1.9	53
259	Superhydrophobic and oleophobic fibers by coaxial electrospinning. *Langmuir*, **2009**, 25, 9454-62	4	265
258	Role of surfactants in the interaction of dye molecules in natural DNA polymers. *Langmuir*, **2009**, 25, 11698-702	4	29
257	Optical and structural characterization of blue-emitting Mg2+- and Zn2+-doped GaN nanoparticles. *Journal of Materials Chemistry*, **2009**, 19, 3889		9
256	High speed nanofluidic protein accumulator. *Lab on A Chip*, **2009**, 9, 1890-6	7.2	58
255	A nearly ideal phosphor-converted white light-emitting diode. *Applied Physics Letters*, **2008**, 92, 143309	3.4	234
254	I-V and Gain Characteristics of Electrowetting-Based Liquid Field Effect Transistor **2008**,		1
253	Effect of Si and Er Co-doping on Green Electroluminescence from GaN:Er ELDs. *Materials Research Society Symposia Proceedings*, **2008**, 1068, 1		
252	Versatile Core-Sheath Biofibers using Coaxial Electrospinning. *Materials Research Society Symposia Proceedings*, **2008**, 1094, 1		21
251	Direct write electron beam patterning of DNA complex thin films. *Journal of Vacuum Science & Technology B*, **2008**, 26, 2567-2571		4
250	Chirality of sulforhodamine dye molecules incorporated in DNA thin films. *Applied Physics Letters*, **2008**, 93, 193903	3.4	11
249	Dynamics of ultraviolet emissions in Tm-doped AlN using above band gap excitation. *Applied Physics Letters*, **2008**, 93, 061110	3.4	14
248	Mg 2+-doped GaN nanoparticles as blue-light emitters: a method to avoid sintering at high temperatures. *Small*, **2008**, 4, 105-10	11	10
247	Effect of process conditions on gain and loss in GaN:Eu cavities on different substrates. *Physica Status Solidi (A) Applications and Materials Science*, **2008**, 205, 26-29	1.6	6
246	Stimulated emission of sulforhodamine 640 doped DNA distributed feedback (DFB) laser devices **2007**,		2
245	A comparative study of electrode effects on the electrical and luminescent characteristics of Alq3/TPD OLED: Improvements due to conductive polymer (PEDOT) anode. *Journal of Luminescence*, **2007**, 126, 225-229	3.8	56
244	Prospects for rare earth doped GaN lasers on Si. *Materials Today*, **2007**, 10, 20-27	21.8	76
243	Identification of defect-trap-related europium sites in gallium nitride. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2007**, 4, 834-837		4

242	Color tunable organic light emitting diodes using Eu complex doping. *Solid-State Electronics*, **2007**, 51, 500-504	1.7	17
241	Photoluminescence and lasing from deoxyribonucleic acid (DNA) thin films doped with sulforhodamine. *Applied Optics*, **2007**, 46, 1507-13	1.7	93
240	ELiXIR-Solid-State Luminaire With Enhanced Light Extraction by Internal Reflection. *Journal of Display Technology*, **2007**, 3, 155-159		50
239	Molecular beam deposition of DNA nanometer films. *Nano Letters*, **2007**, 7, 133-7	11.5	35
238	Spectroscopic and energy transfer studies of Eu3+ centers in GaN. *Journal of Applied Physics*, **2007**, 102, 073520	2.5	46
237	Liquid-state field-effect transistors using electrowetting. *Applied Physics Letters*, **2007**, 90, 043507	3.4	16
236	Correlation between compositional fluctuation and magnetic properties of Tm-doped AlGaN alloys. *Applied Physics Letters*, **2007**, 91, 222503	3.4	23
235	Visible lasing from GaN:Eu optical cavities on sapphire substrates. *Optical Materials*, **2006**, 28, 859-863	3.3	9
234	GaN:Eu electroluminescent devices grown by interrupted growth epitaxy. *Thin Solid Films*, **2006**, 496, 636-642	2.2	20
233	Magnetic and Optical Properties of Eu-doped GaN. *Materials Research Society Symposia Proceedings*, **2006**, 955, 1		
232	Optical and magnetic properties of Eu-doped GaN. *Applied Physics Letters*, **2006**, 89, 132119	3.4	69
231	Site specific Eu3+ stimulated emission in GaN host. *Applied Physics Letters*, **2006**, 88, 011111	3.4	19
230	Enhanced emission efficiency in organic light-emitting diodes using deoxyribonucleic acid complex as an electron blocking layer. *Applied Physics Letters*, **2006**, 88, 171109	3.4	259
229	Organic light emitting diode with a DNA biopolymer electron blocking layer **2006**,		2
228	Growth temperature dependence of optical modal gain and loss in GaN:Eu active medium on Si. *Optics Express*, **2006**, 14, 5307-12	3.3	3
227	Maximizing Alq/sub 3/ OLED internal and external efficiencies: charge balanced device structure and color conversion outcoupling lenses. *Journal of Display Technology*, **2006**, 2, 143-152		55
226	Extended X-ray absorption fine structure studies of GaN epilayers doped with Er. *Optical Materials*, **2006**, 28, 785-789	3.3	9
225	DNA-based materials for electro-optic applications: current status **2005**, 5934, 38		7

224	High-transmission electrowetting light valves. *Applied Physics Letters*, **2005**, 86, 151121	3.4	53
223	Light wave coupled flat panel displays and solid-state lighting using hybrid inorganic/organic materials. *Journal of Display Technology*, **2005**, 1, 157-166		11
222	Optical properties of Er in Er-doped Zn/sub 2/Si/sub 0.5/Ge/sub 0.5/O/sub 4/ waveguide amplifiers. *Journal of Lightwave Technology*, **2005**, 23, 1342-1349	4	5
221	Molecular binding and enhanced photoluminescence of bromocresol purple in marine derived DNA **2005**,		1
220	56.3: Electrowetting Light Valves with Greater than 80% Transmission, Unlimited View Angle, and Video Response. *Digest of Technical Papers SID International Symposium*, **2005**, 36, 1674	0.5	4
219	P-117: Electrowetting-Based Pixelation for Light Wave Coupling Displays. *Digest of Technical Papers SID International Symposium*, **2005**, 36, 746	0.5	2
218	High brightness ZnS and GaN electroluminescent devices using PZT thick dielectric layers. *IEEE Transactions on Electron Devices*, **2005**, 52, 194-203	2.9	12
217	Spectroscopic studies of the infrared emission from Tm doped AlxGa1−xN thin films. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 2796-2799		1
216	Transmission electron microscopy of GaN layers in-situ doped with Er during plasma assisted MBE. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 2484-2487		3
215	Cathodoluminescence and its temperature dependence in Tm-doped AlxGa1−xN thin films. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 2765-2769		1
214	Intense switchable fluorescence in light wave coupled electrowetting devices. *Applied Physics Letters*, **2005**, 86, 011105	3.4	31
213	Effect of optical excitation energy on the red luminescence of Eu3+ in GaN. *Applied Physics Letters*, **2005**, 86, 051110	3.4	37
212	On 2.7 μm Emission from Er-doped Large Bandgap Hosts. *Materials Research Society Symposia Proceedings*, **2005**, 866, 7		5
211	GaN:Eu Interrupted Growth Epitaxy (IGE): Thin Film Growth and Electroluminescent Devices. *Materials Research Society Symposia Proceedings*, **2005**, 866, 53		7
210	Excitation-Wavelength Dependent and Time-Resolved Photoluminescence Studies of Europium Doped GaN Grown by Interrupted Growth Epitaxy (IGE). *Materials Research Society Symposia Proceedings*, **2005**, 866, 1		14
209	Laser action in Eu-doped GaN thin-film cavity at room temperature. *Applied Physics Letters*, **2004**, 85, 4588-4590	3.4	89
208	Temperature dependence of energy transfer mechanisms in Eu-doped GaN. *Journal of Applied Physics*, **2004**, 95, 7717-7724	2.5	51
207	Optical amplification and electroluminescence at 1.54 μm in Er-doped zinc silicate germanate on silicon. *Applied Physics Letters*, **2004**, 84, 1462-1464	3.4	23

206	Photoluminescence and excitation spectroscopy of the 1.5□□m Er-related band in MBE-grown GaN layers. *Superlattices and Microstructures*, **2004**, 36, 701-705	2.8	5
205	P-59: A Novel Fluorescent Display Using Light Wave Coupling Technology. *Digest of Technical Papers SID International Symposium*, **2004**, 35, 470	0.5	2
204	New spectroscopic data of erbium ions in GaN thin films. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2003**, 105, 126-131	3.1	7
203	SiC thin-film Fabry-Perot interferometer for fiber-optic temperature sensor. *IEEE Transactions on Electron Devices*, **2003**, 50, 2159-2164	2.9	22
202	Photoluminescence studies of rare earth (Er, Eu, Tm) in situ doped GaN. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2003**, 105, 91-96	3.1	73
201	Spectral and time-resolved photoluminescence studies of Eu-doped GaN. *Applied Physics Letters*, **2003**, 82, 1655-1657	3.4	121
200	Selective enhancement of blue electroluminescence from GaN:Tm. *Applied Physics Letters*, **2003**, 82, 55-57	3.4	17
199	Red emission from Eu-doped GaN luminescent films grown by metalorganic chemical vapor deposition. *Applied Physics Letters*, **2003**, 83, 9-11	3.4	59
198	Effect of trimethylsilane flow rate on the growth of SiC thin-films for fiber-optic temperature sensors. *Journal of Microelectromechanical Systems*, **2003**, 12, 797-803	2.5	3
197	Three-color integration on rare-earth-doped GaN electroluminescent thin films. *Applied Physics Letters*, **2003**, 82, 502-504	3.4	101
196	Photoluminescence properties of in situ Tm-doped AlxGa1□N. *Applied Physics Letters*, **2003**, 83, 4556-4558	3.4	51
195	Enhanced blue emission from Tm-doped AlxGa1□N electroluminescent thin films. *Applied Physics Letters*, **2003**, 83, 2094-2096	3.4	47
194	Fluorescence Dynamics of Er3+ Ions in MBE-Grown GaN-Thin Films **2003**, 109-124		1
193	Rare-earth-doped GaN: growth, properties, and fabrication of electroluminescent devices. *IEEE Journal of Selected Topics in Quantum Electronics*, **2002**, 8, 749-766	3.8	233
192	Focused ion beam fabricated micrograting for integrated optics applications. *IEEE Journal of Selected Topics in Quantum Electronics*, **2002**, 8, 1323-1330	3.8	6
191	Photoluminescent and electroluminescent Zn/sub 2/Si/sub 0.5/Ge/sub 0.5/O/sub 4/:Mn thin films for integrated optic devices. *IEEE Journal of Selected Topics in Quantum Electronics*, **2002**, 8, 1420-1426	3.8	13
190	Temperature behavior of visible and infrared electroluminescent devices fabricated on erbium-doped GaN. *IEEE Transactions on Electron Devices*, **2002**, 49, 48-54	2.9	27
189	Contrast-enhancement in black dielectric electroluminescent devices. *IEEE Transactions on Electron Devices*, **2002**, 49, 1348-1352	2.9	3

188	Rare-earth-doped GaN switchable color electroluminescent devices. *IEEE Transactions on Electron Devices*, **2002**, 49, 1545-1551	2.9	17
187	Growth and doping of SiC-thin films on low-stress, amorphous Si3N4/Si substrates for robust microelectromechanical systems applications. *Journal of Electronic Materials*, **2002**, 31, 361-365	1.9	11
186	Enhanced blue and green emission in rare-earth-doped GaN electroluminescent devices by optical photopumping. *Applied Physics Letters*, **2002**, 81, 2331-2333	3.4	39
185	Lateral color integration on rare-earth-doped GaN electroluminescent thin films. *Applied Physics Letters*, **2002**, 80, 1888-1890	3.4	30
184	Growth-temperature dependence of Er-doped GaN luminescent thin films. *Applied Physics Letters*, **2002**, 80, 344-346	3.4	8
183	In-situ Er-doped GaN optical storage devices using high-resolution focused ion beam milling. *Optical Engineering*, **2002**, 41, 742	1.1	12
182	Electroluminescent devices using a high-temperature stable GaN-based phosphor and thick-film dielectric layer. *IEEE Transactions on Electron Devices*, **2002**, 49, 557-563	2.9	11
181	Ga flux dependence of Er-doped GaN luminescent thin films. *Applied Physics Letters*, **2002**, 80, 728-730	3.4	22
180	Thermal quenching of photoluminescence from Er-doped GaN thin films. *Journal of Alloys and Compounds*, **2002**, 341, 62-66	5.7	13
179	Spectroscopic studies of the visible and infrared luminescence from Er doped GaN. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2001**, 81, 116-120	3.1	23
178	Multiple color capability from rare earth-doped gallium nitride. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2001**, 81, 97-101	3.1	81
177	Mg□a liquid metal ion source for implantation doping of GaN. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2001**, 19, 2551		4
176	GaN focused ion beam micromachining with gas-assisted etching. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2001**, 19, 2547		25
175	Room-temperature-grown rare-earth-doped GaN luminescent thin films. *Applied Physics Letters*, **2001**, 79, 1962-1964	3.4	23
174	Optimum Er concentration for in situ doped GaN visible and infrared luminescence. *Applied Physics Letters*, **2001**, 79, 719-721	3.4	38
173	High-Density Er-Implanted GaN Optical Memory Devices. *Applied Optics*, **2001**, 40, 3552-8	1.7	12
172	Digital thin-film color optical memory. *Applied Physics Letters*, **2001**, 78, 255-257	3.4	1
171	AC Operation of GaN:Er Thin Film Electroluminescent Display Devices. *Materials Research Society Symposia Proceedings*, **2000**, 639, 1041		1

170	RBS/Channeling study of Er doped GaN films grown by MBE on Si substrates. *Nuclear Instruments & Methods in Physics Research B*, **2000**, 161-163, 946-951	1.2	21
169	CW blue-green light emission from GaN and SiC by sum-frequency generation and second harmonic generation. *Journal of Electronic Materials*, **2000**, 29, 1059-1062	1.9	4
168	Formation of SiC SOI Structures by Direct Growth on Insulating Layers. *Journal of the Electrochemical Society*, **2000**, 147, 3845	3.9	10
167	Voltage-controlled yellow or orange emission from GaN codoped with Er and Eu. *Applied Physics Letters*, **2000**, 76, 1525-1527	3.4	70
166	Low-voltage GaN:Er green electroluminescent devices. *Applied Physics Letters*, **2000**, 76, 1365-1367	3.4	32
165	Alternating current thin-film electroluminescence of GaN:Er. *Applied Physics Letters*, **2000**, 77, 3520-3522	3.4	11
164	Local structure and bonding of Er in GaN: A contrast with Er in Si. *Applied Physics Letters*, **2000**, 76, 2865-2867	3.4	52
163	Photoluminescence studies and read/write process of a strong two-photon absorbing chromophore. *Applied Physics Letters*, **2000**, 77, 328-330	3.4	25
162	In Situ N[sub 2]-Doping of SiC Films Grown on Si(111) by Chemical Vapor Deposition from Organosilanes. *Journal of the Electrochemical Society*, **2000**, 147, 2324	3.9	15
161	CMOS-based photoreceiver arrays for page-oriented optical storage access. *IEEE Photonics Technology Letters*, **2000**, 12, 1234-1236	2.2	4
160	Comparison of the Optical Properties of Er3+ Doped Gallium Nitride Prepared by Metalorganic Molecular Beam Epitaxy (Mombe) and Solid Source Molecular Beam Epitaxy (SSMBE). *MRS Internet Journal of Nitride Semiconductor Research*, **2000**, 5, 824-830		2
159	Focused Ion Beam Micromachining of GaN Photonic Devices. *MRS Internet Journal of Nitride Semiconductor Research*, **1999**, 4, 920-925		1
158	Development of an Er□Ni liquid alloy ion source. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1999**, 17, 1056		12
157	Focused ion beam micromilling of GaN and related substrate materials (sapphire, SiC, and Si). *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1999**, 17, 362		37
156	Growth and morphology of Er-doped GaN on sapphire and hydride vapor phase epitaxy substrates. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1999**, 17, 1195		17
155	Damage generation and removal in the Ga+ focused ion beam micromachining of GaN for photonic applications. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1999**, 17, 3063		26
154	Rare earth focused ion beam implantation utilizing Er and Pr liquid alloy ion sources. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1999**, 17, 2791		14
153	Heteroepitaxial Growth of SiC on Si(100) and (111) by Chemical Vapor Deposition Using Trimethylsilane. *Journal of the Electrochemical Society*, **1999**, 146, 1197-1202	3.9	64

152	Photonic Applications of Rare-Earth-Doped Materials. *MRS Bulletin*, **1999**, 24, 16-20	3.2	27
151	Red light emission by photoluminescence and electroluminescence from Pr-doped GaN on Si substrates. *Applied Physics Letters*, **1999**, 74, 2161-2163	3.4	114
150	Visible and infrared rare-earth-activated electroluminescence from indium tin oxide Schottky diodes to GaN:Er on Si. *Applied Physics Letters*, **1999**, 74, 182-184	3.4	75
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